

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the application of:

Hideyuki MATSUOKA et al.

Appln. No.:

Group Art Unit:

Filed: HERewith

For: MAGNETIC SEMICONDUCTOR MEMORY DEVICE

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INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Pursuant to 37 C.F.R. § 1.56, and without any
assertion as to materiality or prior art effect, the
documents listed on the attached Form PTO-1449 are hereby
cited.


Document AP on the attached List was cited in the
specification, on page 1, and its relevance is indicated
therein. Document AA is the U.S. counterpart of Document
AJ.

Respectfully submitted,

MWS:lat

Miles & Stockbridge P.C.
1751 Pinnacle Drive
Suite 500
McLean, Virginia 22102-3833
(703) 903-9000

By:


Mitchell W. Shapiro
Reg. No. 31,568

November 19, 2003

FORM PTO-1449				Atty. Docket No. XA-9989		Appln. No.	
LIST OF DOCUMENTS CITED BY APPLICANT							
				Applicant Hideyuki MATSUOKA et al.			
				Filing Date HEREWITH		Group	
U.S. PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Name	Class	Sub-class	Filing Date
	AA	2002-0093845	7/18/02	Matsuoka et al.	365	97	
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
FOREIGN PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Country	Class	Sub-class	Translation
	AJ	2002-208682	7/26/02	Japan			Abstract
	AK						
	AL						
	AM						
	AN						
	AO						
OTHER (including author, title, date, pertinent pages, etc.)							
	AP	Durlam et al., "A low power 1Mbit MRAM based on 1T1MTJ bit cell integrated with Copper Interconnects," 2002 Symposium on VLSI Circuits Digest of Technical Papers, pp. 160-163.					
	AQ						
	AR						
Examiner				Date Considered			
XAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.							